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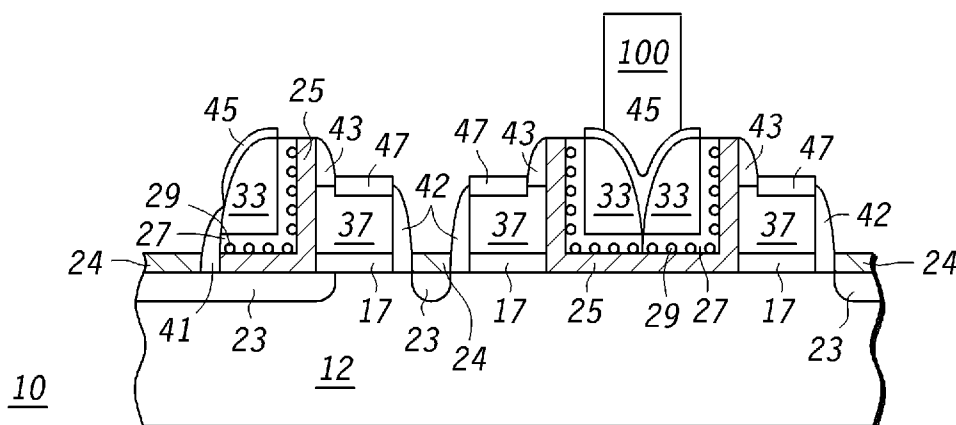
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ance Notes on Codes and Abbreviations" appearing at the begin-
ning of each regular issue of the PCT Gazette.

(54) Title: SILICIDED NONVOLATILE MEMORY AND METHOD OF MAKING SAME



(57) Abstract: A memory device (10) is formed on a semiconductor substrate (12). A select gate electrode (37) and a control gate electrode (33) are formed adjacent to one another. One of either the select gate electrode (37) or the control gate electrodes (33) is recessed with respect to the other. The recess allows for a manufacturable process with which to form silicided surfaces on both the select gate electrode and the control gate electrode.

INTERNATIONAL SEARCH REPORT

International application No.
PCT/US 07/62540

A. CLASSIFICATION OF SUBJECT MATTER

IPC(8) - H01L21/762 (2007.01)

USPC - 257/E21.552

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)
257/E21.552

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched
USPC: 257/315, 257/E21.682, 257/E21.69, 257/E27.103 (text search, see terms below)
Google Scholar Internet, DialogPRO - see keywords below

Electronic data base consulted during the international search (name of data base and, where practicable, search terms used)

PubWEST(USPT,PGPB,EPAB,JPAB); DialogPRO(Engineering); Google Scholar

Search Terms: nonvolatile memory, silicided, silicon, gate, recess, source, drain, etch, polish, spacer, substrate

C. DOCUMENTS CONSIDERED TO BE RELEVANT

Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
X ----- Y	US 2006/0017094 A1 (Kim et al.) 26 January 2006 (26.01.2006), entire document, especially para [0007]-[0009], [0041], [0045]-[0046] and [0069]	1, 4-9, 11-13, 15 and 18-20 ----- 2-3, 10, 14 and 16-17
Y	US 2005/0176202 A1 (Hisamoto et al.) 11 August 2005 (11.08.2005), para [0018]	2-3, 10, 14 and 16
Y	US 2005/0180210 A1 (Harari et al.) 18 August 2005 (18.08.2005), Abstract and para [0150]	17

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